

C3D03060E-Silicon Carbide Schottky Diode

Z-Rec[™] Rectifier

$$\mathbf{V}_{\mathbf{RRM}}$$
 = 600 V
 $\mathbf{I}_{\mathbf{F}(\mathbf{AVG})}$ = 3 A
 $\mathbf{Q}_{\mathbf{c}}$ = 6.7 nC

Features

- 600-Volt Schottky Rectifier
- Optimized for PFC Boost Diode Application
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on V_F

Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

- Switch Mode Power Supplies
 - Power Factor Correction - Typical PFC P_{out}: 300W-450W

Package





Part Number	Package	Marking
C3D03060E	TO-252-2	C3D03060

Maximum Ratings

Symbol	Parameter	Value	Unit	Test Conditions	Note
V _{RRM}	Repetitive Peak Reverse Voltage	600	V		ĺ
V _{RSM}	Surge Peak Reverse Voltage	600	V		
V _{DC}	DC Blocking Voltage	600	V		
$\mathbf{I}_{\mathrm{F}(\mathrm{AVG})}$	Average Forward Current	3.0	А	T _c =160°C	
\mathbf{I}_{FRM}	Repetitive Peak Forward Surge Current	18 13.5	А	$T_c=25$ °C, $t_p=10$ mS, Half Sine Wave D=0.3 $T_c=110$ °C, $t_p=10$ mS, Half Sine Wave D=0.3	
\mathbf{I}_{FSM}	Non-Repetitive Peak Forward Surge Current	26 23	А	$T_c=25$ °C, $t_p=10$ mS, Half Sine Wave D=0.3 $T_c=110$ °C, $t_p=10$ mS, Half Sine Wave D=0.3	
\mathbf{I}_{FSM}	Non-Repetitive Peak Forward Surge Current	100	А	$T_c=25^{\circ}C$, $t_p=10 \ \mu$ S, Pulse	
P_{tot}	Power Dissipation	53 23	W	$T_c = 25^{\circ}C$ $T_c = 110^{\circ}C$	
T_{j} , T_{stg}	Operating Junction and Storage Temperature	-55 to +175	°C		



Electrical Characteristics

Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
V _F	Forward Voltage		1.7 2.4	V	$I_{F} = 3 A T_{J} = 25^{\circ}C$ $I_{F} = 3 A T_{J} = 175^{\circ}C$	
I _R	Reverse Current	10 20	50 100	μA	$V_{R} = 600 V T_{J} = 25^{\circ}C$ $V_{R} = 600 V T_{J} = 175^{\circ}C$	
Q _c	Total Capacitive Charge	6.7		nC	$V_{R} = 600 \text{ V}, I_{F} = 3\text{A}$ $di/dt = 500 \text{ A}/\mu\text{S}$ $T_{J} = 25^{\circ}\text{C}$	
С	Total Capacitance	155 13 12		pF	$ \begin{array}{l} V_{_R} = 0 \ V, \ T_{_J} = 25 \ ^\circ C, \ f = 1 \ MHz \\ V_{_R} = 200 \ V, \ T_{_J} = 25 \ ^\circ C, \ f = 1 \ MHz \\ V_{_R} = 400 \ V, \ T_{_J} = 25 \ ^\circ C, \ f = 1 \ MHz \end{array} $	

Note:

1. This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

S	ymbol	Parameter	Тур.	Unit
	$R_{_{\theta JC}}$	TO-252 Package Thermal Resistance from Junction to Case	2.8	°C/W

Typical Performance

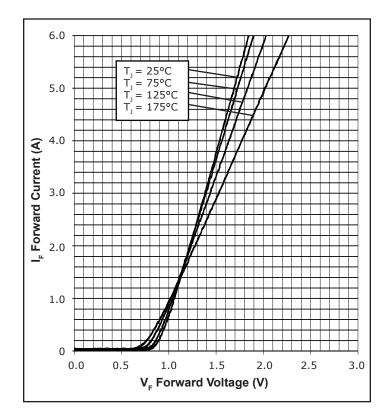


Figure 1. Forward Characteristics

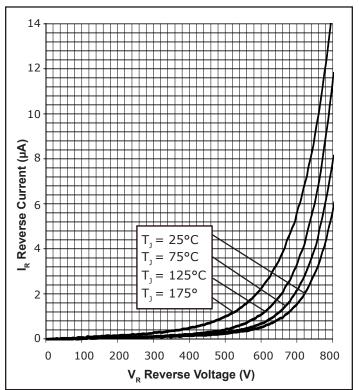


Figure 2. Reverse Characteristics



Typical Performance

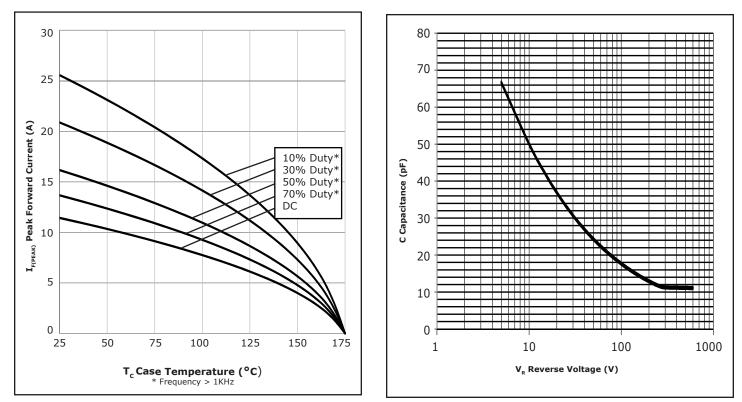


Figure 3. Current Derating

Figure 4. Capacitance vs. Reverse Voltage

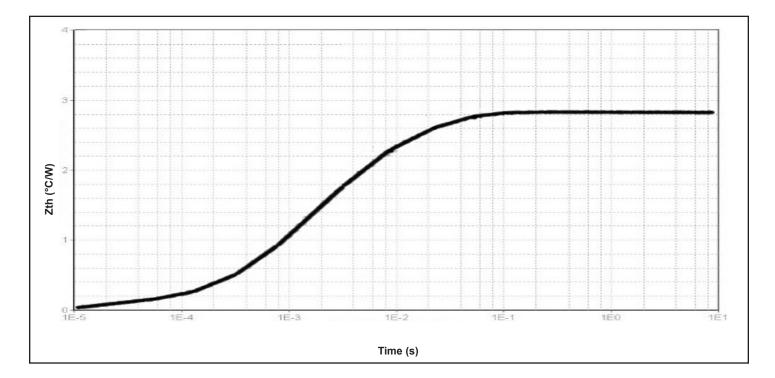


Figure 5. Transient Thermal Impedance



Typical Performance

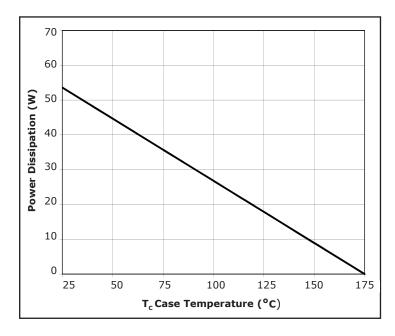
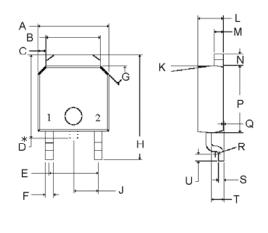


Figure 6. Power Derating

Package Dimensions

Package TO-252-2







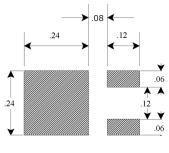
DOC	Inc	hes	Millimeters			
POS	Min	Мах	Min	Мах		
А	.255	.265	6.477	6.731		
В	.197	.205	5.004	5.207		
С	.027	.033	.686	.838		
D*	.270	.322	6.858	8.179		
E	.178	.182	4.521	4.623		
F	.025	.035	.635	.889		
G	44°	46°	44°	46°		
Н	.382	.397	9.703	10.084		
J	.090	.090 TYP		2.286 TYP		
К	6°	8°	6°	8°		
L	.086	.094	2.184	2.388		
М	.030	.034	.762	.864		
Ν	.040	.044	1.016	1.118		
Р	.235	.245	5.969	6.223		
Q	0.00	.004	0.00	.102		
R	R0.01 TYP		R0.31 TYP			
S	.017	.023	.428	.588		
Т	.040	.044	1.016	1.118		
U	.021	.027	.534	1.118		

Note:

* Tab "D" may not be present



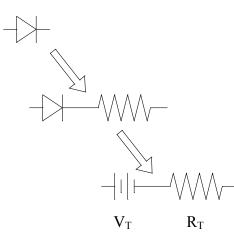
Recommended Solder Pad Layout





Part Number	Package	Marking
C3D03060E	TO-252-2	C3D03060

Diode Model



 $V_{T} = V_{T} + If^{*}R_{T}$

$$V_{T} = 1.01 + (T_{J}^{*} - 1.26^{*}10^{-3})$$

$$R_{T} = 0.14 + (T_{J}^{*} 1.13^{*}10^{-3})$$

Note: T_j = Diode Junction Temperature In Degrees Celcius

"The levels of environmentally sensitive, persistent biologically toxic (PBT), persistent organic pollutants (POP), or otherwise restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2002/95/EC on the restriction of the use of certain hazardous substances in electrical and electronic equipment (RoHS), as amended through April 21, 2006.

This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control systems, air traffic control systems, or weapons systems.

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